

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hark C. Chan.) Examiner: Unknown
)
Serial No.: divisional of 10/262,728) Group Art Unit: Unknown
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Filed: Herewith)
)
For: Shunt Connection to Emitter)
)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

Listed on the attached Form PTO-1449 is information known to applicant. Each reference cited herein was previously cited in parent applications and a copy of each reference was provided to the Examiner, or cited by the Examiner in an Office Action. No additional copies of the references are being submitted with this paper, but will be furnished upon the Examiner's request.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP 609.

This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in section 1.56.

Respectfully submitted,

Date: Oct. 9, 200


Hark C. Chan
(Reg. N.: 35,477)

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Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Application Number	
Sheet	1	of	2
		Examiner Name	Andrew Horch
		Art Unit	
		Attorney Docket Number	C018-D-1

U. S. PATENT DOCUMENTS				
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number-Kind Code ² (<i>if known</i>)		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US- 3,943,549	3-9-1976	Jaecklin et al.
		US- 4,165,517	8-21-1979	Temple et al.
		US- 4,281,336	7-28-1981	Sommer et al.
		US- 4,323,793	4-6-1982	Schutten et al.
		US- 4,646,121	2-24-1987	Ogura
		US- 4,829,357	5-9-1989	Kasahara
		US- 4,864,168	9-5-1989	Kasahara et al.
		US- 4,982,258	1-1-1991	Baliga
		US- 5,412,228	5-2-1995	Baliga
		US- 5,463,344	10-31-1995	Temple
		US- 5,606,186	02-1997	Noda, Minoru
		US- 4,825,272	04-1989	Lehmann, Erhard
		US- 6,104,045	8-15-2000	Forbes et al.
		US- 6,225,165	5-1-2001	Noble, et al.
		US- 6,229,161	5-8-2001	Nemati et al.
		US-		

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Country Code ³ "Number" Kind Code ⁵ (<i>if known</i>)		Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
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Examiner Signature	Date Considered
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Substitute for form 1449/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Application Number	
				Filing Date	
				First Named Inventor	Andrew Horch
				Art Unit	
				Examiner Name	
Sheet 2	of 2	Attorney Docket Number	C018-D-1		

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
		K. DeMeyer, S. Kubicek and H. van Meer, Raised Source/Drains with Disposable Spacers for sub 100 nm CMOS Technologies, Extended Abstracts of International Workshop on Junction Technology 2001.			
		Mark Rodder and D. Yeakley, Raised Source/Drain MOSFET with Dual Sidewall Spacers, IEEE Electron Device Letters, Vol. 12, No. 3, March 1991			
		Yang-Kyu Choi, Daewon Ha, Tsu-Jae King and Chenming Hu, Nanoscale Ultrathin PMOSFETs with Raised Selective Germanium Source/Drain, IEEE Electron Device Letters, Vol. 22, No. 9, September 2001.			
		N. Lindert, Y. K. Choi, L. Chang, E. Anderson, W. C. Lee, T. J. King, J. Bokor, and C. Hu, Quasi-Planar FinFETs with Selectively Grown Germanium Raised Source/Drain, 2001 IEEE International SOI Conference, 10/2001			
		T. Ohguro, H. Naruse, H. Sugaya, S. Nakamura, E. Morifumi, H. Kimijima, T. Yoshitomi, T. Morimoto, H.S. Momose, Y. Katsumata, and H. Iwai, High Performance RF Characteristics of Raised Gate/Source/Drain CMOS with Co Salicide, 1998 Symposium on VLSI Technology Digest of Technical Papers			
		Hsiang-Jen Huang, Kun-Ming Chen, Tiao-Yuan Huang, Tien-Sheng Chao, Guo-Wei Huang, Chao-Hsin Chien, and Chun-Yen Chang, Improved Low Temperature Characteristics of P-Channel MOSFETs with Si _{1-x} Gex Raised Source and Drain, IEEE Transactions on Electron Devices, Vol. 48, No. 8, August 2001			
		Nemati, Farid and Plummer, James, D., A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, VLSI Technology Technical Digest, 6/1998			
		Nemati, Farid and Plummer, James, D., A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories, International Electron Device Meeting Technical Digest, 1999			
		Gribnikov, Z.S., Korobov, V.A., and Mitin, V.V., The Tunnel Diode as a Thyristor Emitter, Solid-State Electronics, Vol. 42, No. 9, 1998, pp. 1761-1763			

Examiner Signature		Date Considered	
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